Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S13	95	(257/629 or 257/632 or 257/635 or 257/637 or 257/639 or 257/640).ccls. and (photoresist same (oxynitride or SiON or SiNO of SiN or Si3N4 or barrier))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/10 16:49
S14	310	(438/725 or 438/757 or 438/763 or 438/769 or 438/786 or 438/787 or 438/791).ccls. and (photoresist same (oxynitride or SiON or SiNO of SiN or Si3N4 or barrier))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/10 16:49
S18	332	(438/725 or 438/757 or 438/763 or 438/769 or 438/786 or 438/787 or 438/791).ccls. and ((photoresist or photo?resist) same (oxynitride or SiON or SiNO of SiN or Si3N4 or barrier))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/10 16:51
S17	97	(257/629 or 257/632 or 257/635 or 257/637 or 257/639 or 257/640).ccls. and ((photoresist or photo?resist) same (oxynitride or SiON or SiNO of SiN or Si3N4 or barrier))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/10 16:52
S19	334	(438/725 or 438/757 or 438/763 or 438/769 or 438/786 or 438/787 or 438/791).ccls. and ((photoresist$4 or photo?resist$4) same (oxynitride or SiON or SiNO of SiN or Si3N4 or barrier))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/10 16:52
S20	98	(257/629 or 257/632 or 257/635 or 257/637 or 257/639 or 257/640).ccls. and ((photoresist$4 or photo?resist$4) same (oxynitride or SiON or SiNO of SiN or Si3N4 or barrier))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/10 16:52
S6	827	semiconductor and (photoresist same (oxynitride or SiON or SiNO)) and @ad<"19991230"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/10 16:53
S21	1382	semiconductor and (photoresist$4 same (oxynitride or SiON or SiNO or Si3N4 or SiN)) and @ad<"19991230"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/10 16:54
S22	2	("6756634").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/06/13 01:12

S23	11763	semiconductor and mask$4 and (sio or oxide) and (sion or oxynitride) and (sin or nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/08/07 12:42
S25	230	semiconductor and (mask$4 same ((sio or oxide) and (sion or oxynitride) and (sin or nitride))) and @ad<"19951230"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/08/07 12:44
S24	1034	semiconductor and mask$4 and (sio or oxide) and (sion or oxynitride) and (sin or nitride) and @ad<"19951230"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/08/07 22:02
S26	559	semiconductor and mask$4 and (sio or oxide) and (sion or oxynitride) and (sin or nitride) and @ad<"19951230" and photoresist	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/02 01:32
L2	14	semiconductor and (((anti-reflect$5 or antireflect$5 or ARC) with (SION or SiNO or oxynitride)) same (photoresist or resist)) and @ad<"19951230" and photoresist	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/02 02:14
L3	27	semiconductor and ((anti-reflect$5 or antireflect$5 or ARC) with (SION or SiNO or oxynitride)) and (photoresist or resist) and @ad<"19951230" and photoresist	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/02 02:14
L4	13	semiconductor and ((anti-reflect$5 or antireflect$5 or ARC) with (SION or SiNO or oxynitride)) and (photoresist or resist) and @ad<"19951230" and photoresist not L2	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/02 02:14
L6	23	semiconductor and ((anti-reflect$5 or antireflect$5 or ARC) same (SION or SiNO or oxynitride)) and (photoresist or resist) and @ad<"19951230" and photoresist not (L3 or L4)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/02 02:15
L14	8	semiconductor and ((anti-reflect$5 or antireflect$5 or ARC) same (SION or SiNO or oxynitride)) and (photoresist or resist) and @ad<"19951230" not (L2 or L3 or L4 or L5 or L6)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 02:23

L15	18	(semiconductor or substrate) and ((anti-reflect$5 or antireflect$5 or ARC) same (SION or SiNO or oxynitride)) and (photoresist or resist or photolithograph$6 or lithograph$6) and @ad<"19951230" not (L2 or L3 or L4 or L5 or L6)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 02:24
L5	36	semiconductor and ((anti-reflect$5 or antireflect$5 or ARC) same (SION or SiNO or oxynitride)) and (photoresist or resist) and @ad<"19951230" and photoresist not L2	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/02 02:51
L17	60	semiconductor and ((anti-reflect$5 or antireflect$5 or ARC) same (SION or SiNO or oxynitride)) and (mask$5) and @ad<"19951230"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/02 02:52
L18	3	semiconductor and ((anti-reflect$5 or antireflect$5 or ARC) same (SION or SiNO or oxynitride)) and (mask$5) and @ad<"19951230" not (L2 or L3 or L4 or L5 or L6 or L14 or L15 or L16)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/02 02:52
L16	10	(semiconductor or substrate) and ((anti-reflect$5 or antireflect$5 or ARC) same (SION or SiNO or oxynitride)) and (photoresist or resist or photolithograph$6 or lithograph$6) and @ad<"19951230" not (L2 or L3 or L4 or L5 or L6 or L14)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 02:53
L19	6	(semiconductor or substrate) and ((anti-reflect$5 or antireflect$5 or ARC) same (SION or SiNO or oxynitride)) and (mask$4) and @ad<"19951230" not (L2 or L3 or L4 or L5 or L6 or L14)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 02:54
L20	48	(semiconductor or substrate) and ((anti-reflect$5 or antireflect$5 or ARC) same (SION or SiNO or oxynitride)) and @ad<"19951230" not (L2 or L3 or L4 or L5 or L6 or L14)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 02:54